

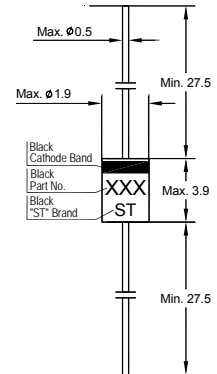
# 1N4150

## Silicon Epitaxial Planar Switching Diode

for general purpose switching applications

### Features

- Fast switching speed
- High reliability



Glass Case DO-35  
Dimensions in mm

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	50	V
Forward Continuous Current	$I_{FM}$	300	mA
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Power Dissipation	$P_{tot}$	500 <sup>1)</sup>	mW
Junction Temperature	$T_j$	200	$^\circ\text{C}$
Operating and Storage Temperature Range	$T_{stg}$	- 65 to + 175	$^\circ\text{C}$

<sup>1)</sup> Valid provided that leads are at a distance of 8 mm from case kept at ambient temperature

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	$V_F$	1.2	V
Reverse Current at $V_R = 50\text{ V}$	$I_R$	100	nA
Reverse Recovery Time at $I_F = I_R = 200\text{ mA}$ , $I_{rr} = 0.1 \times I_R$ , $R_L = 100\ \Omega$	$t_{rr}$	4	ns